

ABSTRACT OF THE DISCLOSURE

A method for producing a microsystem that has, situated on a substrate, a first functional layer that includes a conductive area and a sublayer. Situated on the first functional layer is  
5 a second mechanical functional layer, which is first initially applied onto a sacrificial layer situated and structured on the first functional layer. In addition, a layer is situated on the side of the sublayer facing away from the conductive area. The layer constitutes a protective layer on the first  
10 functional layer that acts in areas during a sacrificial layer etching process so that during removal of the sacrificial layer no etching of the areas of the first functional layer covered by the protective layer occurs, and that in the region of the areas of the first functional layer implemented without  
15 the protective layer the sublayer is removed essentially selectively to the conductive area at the same time as the sacrificial layer. Further, a method is described for producing integrated Microsystems having silicon-germanium functional layers, sacrificial layers containing germanium,  
20 and open metal surfaces. The sacrificial layers containing germanium are at least partially removed in an etching solution, a pH value of the etching solution being kept at least approximately neutral during the etching procedure using a buffer.